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				Application Number	10/8/2,703		
	INFORMATIO	N DISCLOSURE		Filing Date	3/30/04		
STATEMENT BY APPLICANT				First Named Inventor	Park et al.		
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	(000 do many o	nocis as necessary,		Examiner Name	A. Chambliss		
Sheet	1	of	1	Attorney Docket No.	AF01221		

	U.S. PATENT DOCUMENTS								
	U.S. Patent Document		Name of Patentee or	Date of Pub. of					
Exam. Initials*	Cite No.1	Number	Kind Code ² (if known)	Applicant of Cited Doc.	Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant			
AC	AA	5,773,343		Lee et al.	06/30/1998	Entire Document			
AC	AB	6,225,173	B1	Yu	05/01/2001	Entire Document			
	AC								
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	AG								

	FOREIGN PATENT DOCUMENTS								
Exam. Cite		Foreign Patent Document		Name of Patentee	Date of Pub.				
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	ВА								
	6B								
	BF								
L	BG		<u> </u>						

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Exam. Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
AC	CA	*A Novel 0.1µm MOSFET Structure with Inverted Sidewall and Recessed Channel", JEONGHO LYU, BYUNG-GOOK PARK, KUKJIN CHUN and JONG DUK LEE, IEEE Electron Device Letters, volume 17, No. 4, April , 1996, pp. 157-159.	
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